

Part Number: SCP-5887, Rev. –

HV BRIDGE RECTIFIER STACK: 1A 9300V MODULE

Features

- Ideal for HV Power Supply Application
- Excellent Thermal Performance Design
- Isolated base plate: 15KV dc
- Low Mechanical Stress Design
- Contact Factory for Screening options

MAXIMUM RATINGS

(T_J=25°C UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Peak Inverse Voltage and DC Blocking Voltage Per Diode BR1	BV _{CES}	3300	-	-	V
BR2 – BR6		1200	-	-	V
Average Rectified Forward Current Per Diode T _C = 25 °C T _C = 100 °C	I _O	-	-	1	A
				0.2	A
Peak Surge Current Per Diode	I _{FSM}	-	-	25	A
Operating Temperature Range	T _{OP}	- 65	-	175	°C

ELECTRICAL CHARACTERISTICS

(T_J=25°C UNLESS OTHERWISE SPECIFIED)

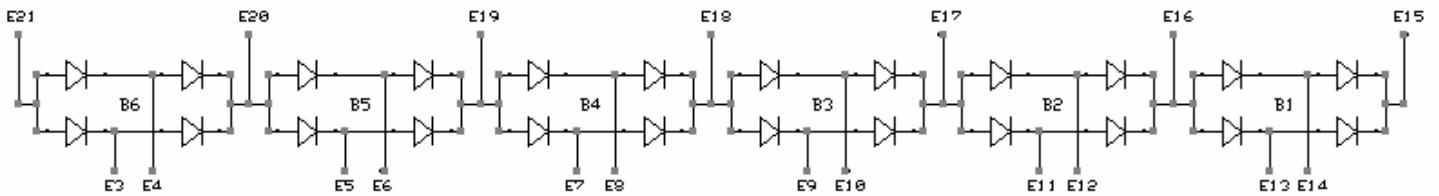
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Instantaneous Forward Voltage I _F = 1A, t _p = 300 μs Pulse BR1	V _{F1}	-	-	7.5	V
BR2 – BR6		-	-	2.5	V
Reverse Leakage Current T _C = 25 °C BR1: V _R = 2500V BR2 – BR6: V _R = 1000V	I _{R1}	-	-	1.0	μA
		-	-	1.0	μA
Reverse Leakage Current T _C = 100 °C BR1: V _R = 2500V BR2 – BR6: V _R = 1000V	I _{R2}	-	-	50	μA
		-	-	50	μA
Breakdown Voltage I _R = 100 μA BR1	B _{VR}	3300	-	-	V
BR2 – BR6		1200	-	-	V
Reverse Recovery Time I _F = 0.5A, I _R = 1.0A , I _{RR} = 0.25A	t _{RR}	-	-	60	ns
Capacitance per Diode V _R = 6V BR1	C _T	-	-	20	pF
BR2 – BR6		-	-	60	pF

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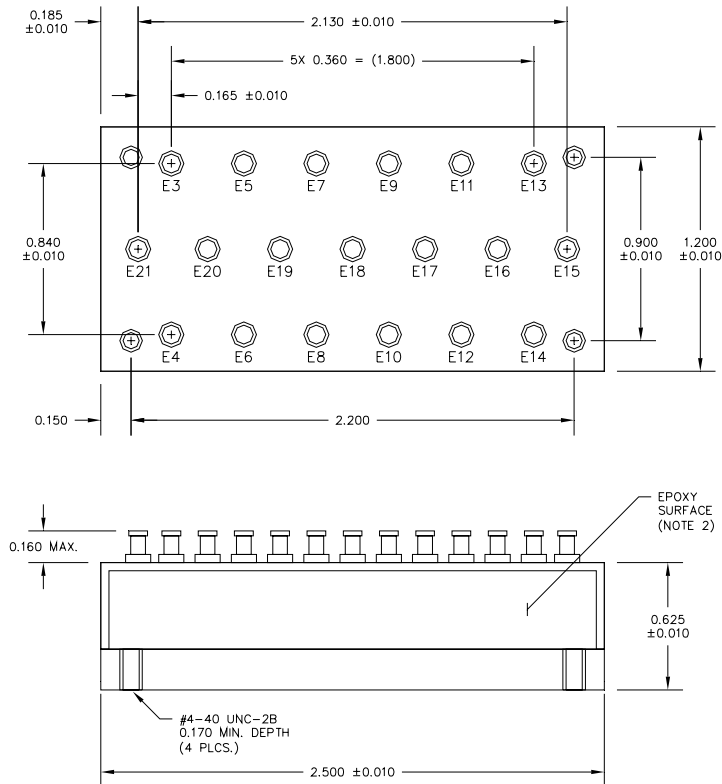
PACKAGE CHARACTERISTICS

Thermal Resistance (Junction to Base)	$R_{\theta JB}$	-	-	2.5	$^{\circ}C/W$
Insulation Resistance: All Terminals to Base @ 15000V	R_{INSUL}	10	-	-	$G\Omega$
Storage Temperature Range	T_{STG}	- 65	-	175	$^{\circ}C$
Isolation to Base Plate	V_{iso}	-	-	15000	V

Schematic Diagram:



Mechanical Outline:



NOTES:
 1) DIMENSIONS UNLESS OTHERWISE NOTED ARE IN INCHES.
 2) POTTING SURFACE UNCONTROLLED.

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